

## 64Mbit SDR I/F FCRAM™

Consumer/Embedded Application Specific Memory for SiP

MB81ES653225-12/-12L

**(Now developing)**

### ■ FEATURES

- 1M words × 32 bits × 2 banks Organization
- Low Power Supply ( $V_{DD} = V_{DDQ} = 1.8 \text{ V} \pm 0.15 \text{ V}$ )
- 1.8 V CMOS I/O Interface
- 8K Refresh Cycles every 32 ms
- Auto- and Self- Refresh
- 2 Banks Operation
- Programmable Burst Type, Burst Length, and CAS Latency
- Burst Read/Write Operation and Burst Read/Single Write Operation Capability
- Programmable Page Length
- Programmable Partial Array Self Refresh (PASR)
- Programmable Temperature Compensated Self Refresh (TCSR)
- Deep Power Down Mode
- Extended Temperature Operation
 

MB81ES653225-12	:	0 °C to 85 °C
MB81ES653225-12L	:	-25 °C to 85 °C
- CKE Power Down Mode
- Byte Control Capability by Data Mask (DQM)
- FCRAM Disable Function for TEST
- FCRAM Self Burn-in Function for TEST
- FCRAM BIST (Built In Self Test) Function for TEST

### ■ PRODUCT OPTIONS

Part Number		MB81ES653225	
		12	12L
Speed Version		12	12L
Clock Frequency (Max)	CL= 2	54 MHz	
	CL= 3	85 MHz	
Burst Mode Cycle Time (Min)	CL= 2	18.5 ns	
	CL= 3	11.7 ns	
Access Time from Clock (Max)	CL= 2	12 ns	
	CL= 3	8.7 ns	